

# IRF6215S/LPbF

- Lead-Free
- Advanced Process Technology
- Surface Mount (IRF6215S)
- Low-profile through-hole (IRF6215L)
- 175°C Operating Temperature
- Fast Switching
- P-Channel
- Fully Avalanche Rated

## Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D<sup>2</sup>Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRF6215L) is available for low-profile applications.

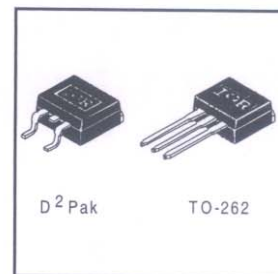
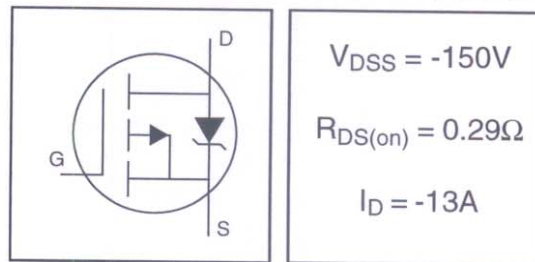
## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V} \textcircled{5}$	-13	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V} \textcircled{5}$	-9.0	
$I_{DM}$	Pulsed Drain Current $\textcircled{1} \textcircled{5}$	-44	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	3.8	W
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	110	W
	Linear Derating Factor	0.71	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy $\textcircled{2} \textcircled{5}$	310	mJ
$I_{AR}$	Avalanche Current $\textcircled{1}$	-6.6	A
$E_{AR}$	Repetitive Avalanche Energy $\textcircled{1}$	11	mJ
$dv/dt$	Peak Diode Recovery $dv/dt \textcircled{3} \textcircled{5}$	-5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient ( PCB Mounted, steady-state)**	—	40	

## HEXFET® Power MOSFET



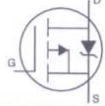
# IRF6215S/LPbF

International  
**IR** Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-150	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.20	—	V/°C	Reference to $25^\circ\text{C}$ , $I_D = -1mA$ ⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.29	$\Omega$	$V_{GS} = -10V, I_D = -6.6A$ ④
		—	—	0.58		$V_{GS} = -10V, I_D = -6.6A$ ④ $T_J = 150^\circ\text{C}$
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$g_{fs}$	Forward Transconductance	3.6	—	—	S	$V_{DS} = -25V, I_D = -6.6A$ ⑤
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-25	$\mu A$	$V_{DS} = 150V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = 120V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = 20V$
$Q_g$	Total Gate Charge	—	—	66	nC	$I_D = -6.6A$
$Q_{gs}$	Gate-to-Source Charge	—	—	8.1		$V_{DS} = -120V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	35		$V_{GS} = -10V$ , See Fig. 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	—	14	—		$V_{DD} = -75V$
$t_r$	Rise Time	—	36	—		$I_D = -6.6A$
$t_{d(off)}$	Turn-Off Delay Time	—	53	—		$R_G = 6.8\Omega$
$t_f$	Fall Time	—	37	—		$R_D = 12\Omega$ , See Fig. 10 ④⑤
$L_S$	Internal Source Inductance	—	7.5	—		nH
$C_{iss}$	Input Capacitance	—	860	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	220	—		$V_{DS} = -25V$
$C_{rss}$	Reverse Transfer Capacitance	—	130	—		$f = 1.0MHz$ , See Fig. 5⑤

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-11	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-44		
$V_{SD}$	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}, I_S = -6.6A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	160	240	ns	$T_J = 25^\circ\text{C}, I_F = -6.6A$
$Q_{rr}$	Reverse Recovery Charge	—	1.2	1.7	$\mu C$	$di/dt = -100A/\mu s$ ③⑤
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 14mH$   
 $R_G = 25\Omega, I_{AS} = -6.6A$ . (See Figure 12)
- ③  $I_{SD} \leq -6.6A, di/dt \leq -620A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .
- ⑤ Uses IRF6215 data and test conditions

\*\* When mounted on 1" square PCB (FR-4 or G-10 Material ).  
For recommended footprint and soldering techniques refer to application note #AN-994.

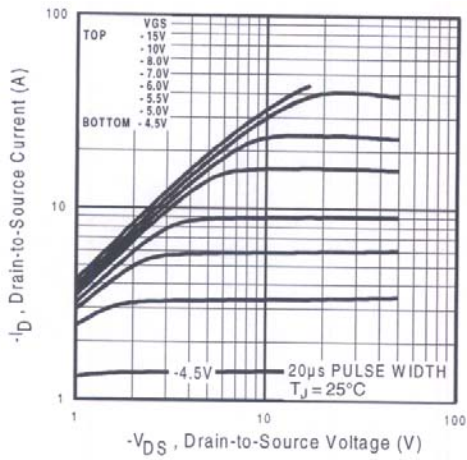


Fig 1. Typical Output Characteristics

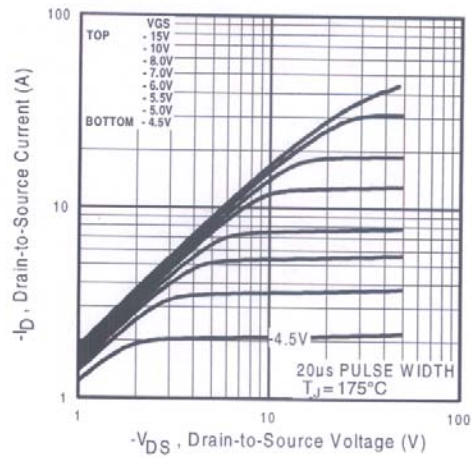


Fig 2. Typical Output Characteristics

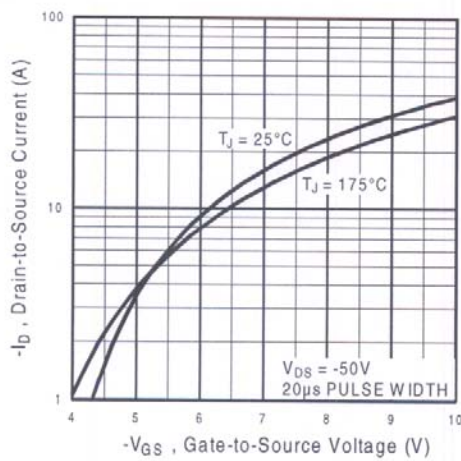


Fig 3. Typical Transfer Characteristics

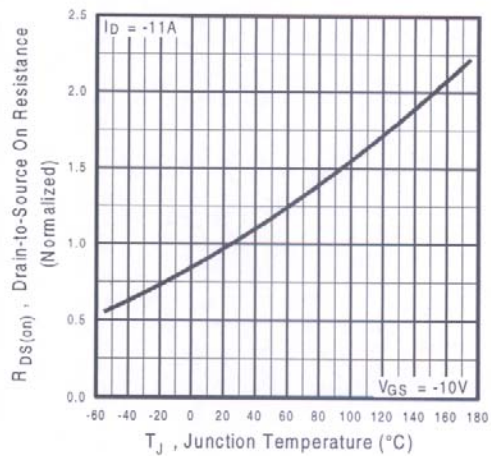
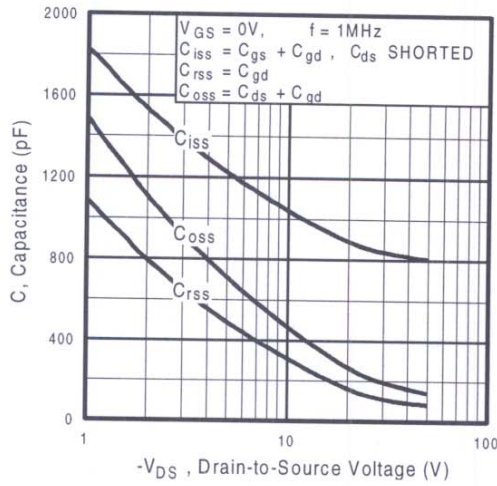
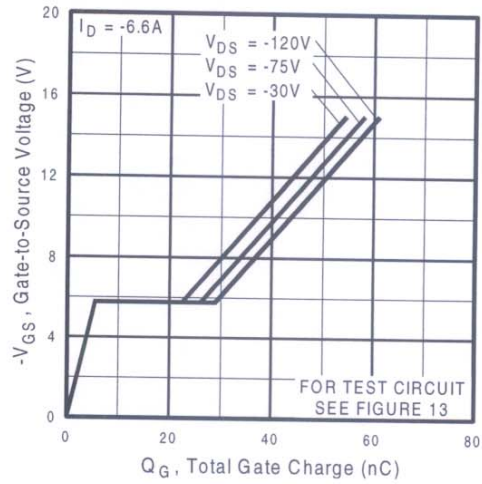


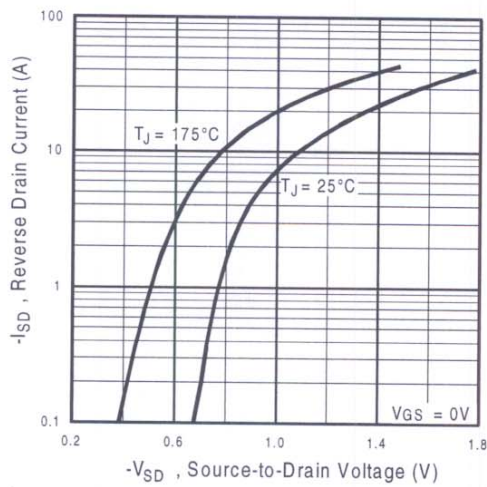
Fig 4. Normalized On-Resistance Vs. Temperature



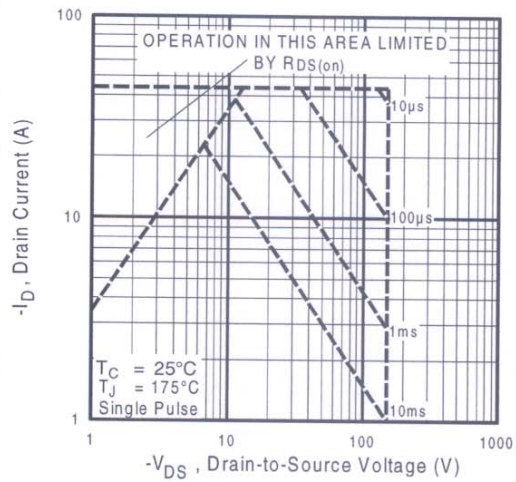
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



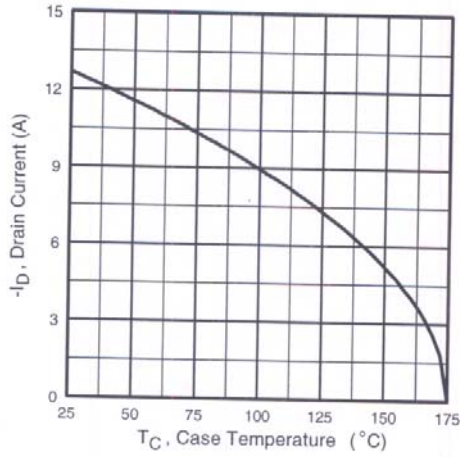
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



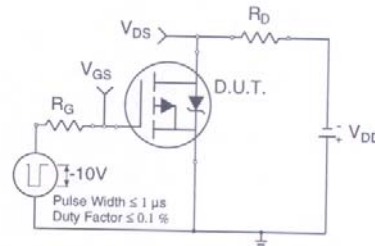
**Fig 7.** Typical Source-Drain Diode Forward Voltage



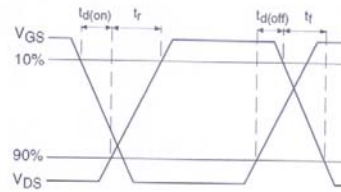
**Fig 8.** Maximum Safe Operating Area



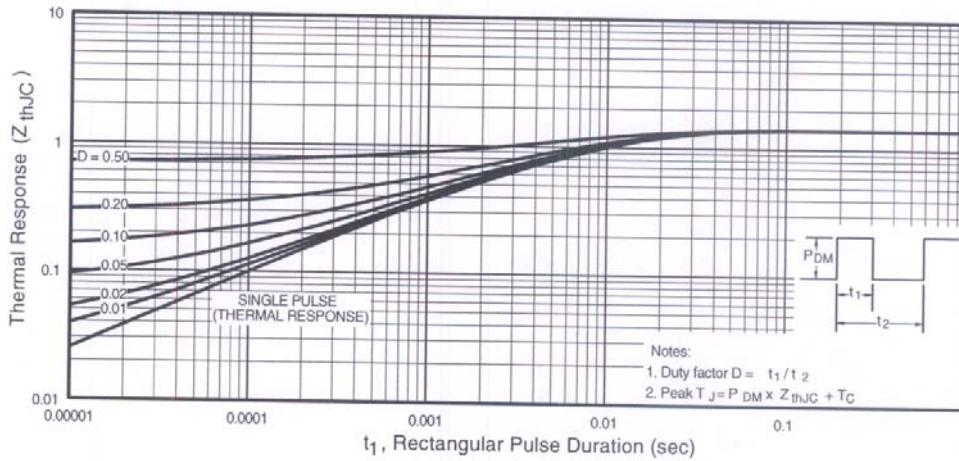
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

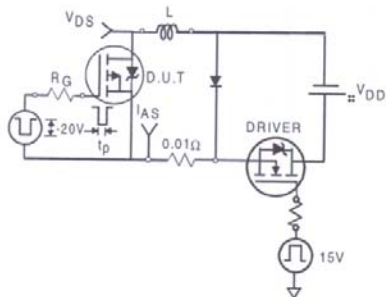


Fig 12a. Unclamped Inductive Test Circuit

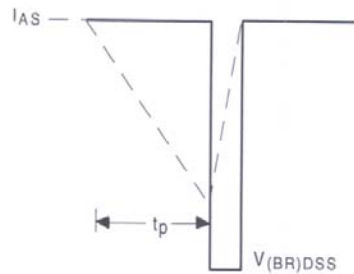


Fig 12b. Unclamped Inductive Waveforms

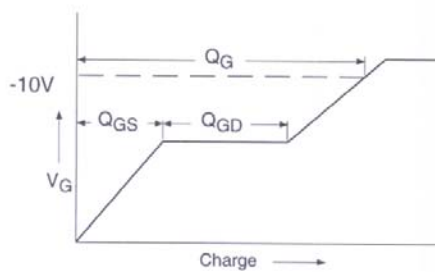


Fig 13a. Basic Gate Charge Waveform

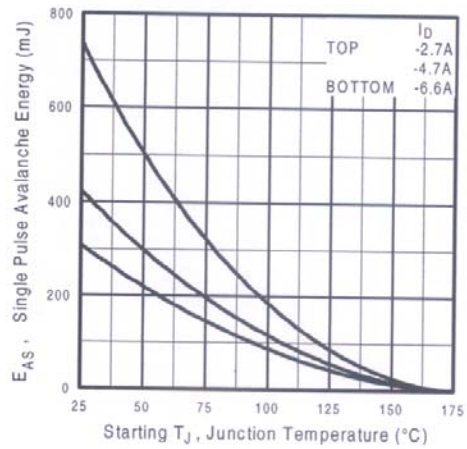


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

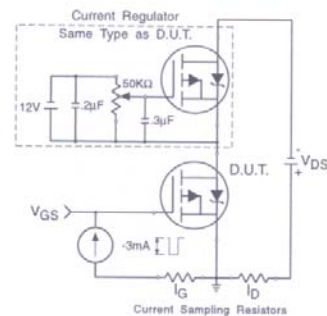
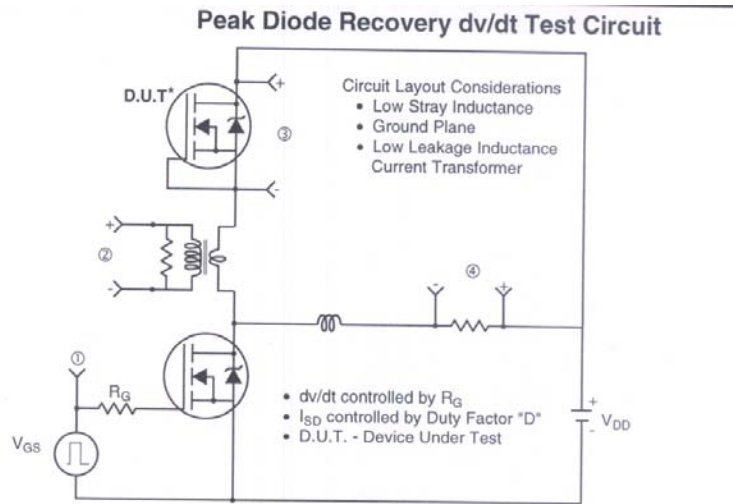
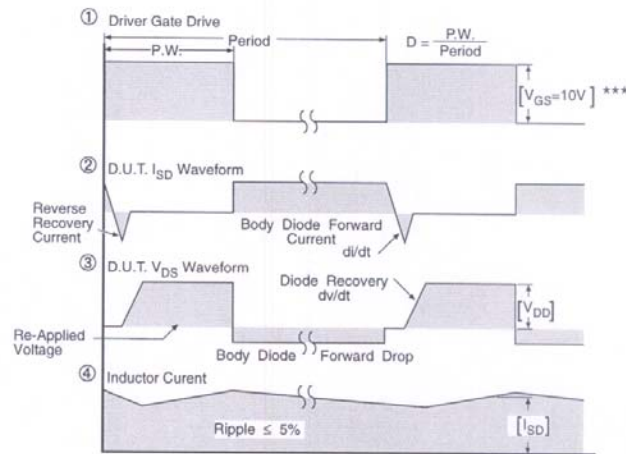


Fig 13b. Gate Charge Test Circuit



\* Reverse Polarity of D.U.T. for P-Channel



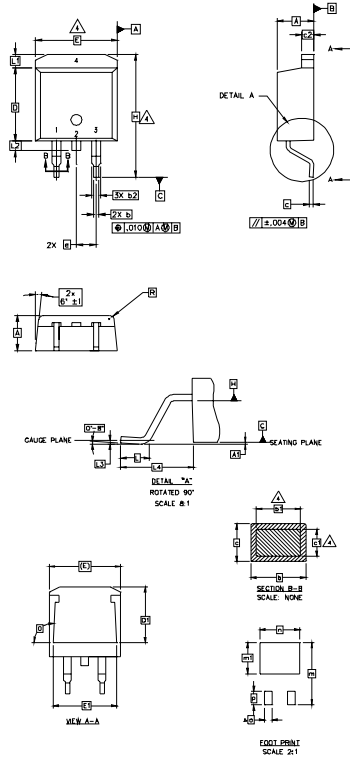
\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig 14.** For P-Channel HEXFETS

# IRF6215S/LPbF

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**IR** Rectifier

## D<sup>2</sup>Pak Package Outline



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  5. CONTROLLING DIMENSION: INCH.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.78	.045	.070	4
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	3
c2	1.14	1.65	.045	.065	
D	8.51	9.65	.335	.380	3
D1	6.86		.270		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		IGBTs, CoPACK
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	1. - GATE 2. 4. - DRAIN 3. - SOURCE
L1		1.65		.065	
L2	1.27	1.78	.050	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	DIODES
m	17.78		.700		
m1	8.89		.350		1. - ANODE *
n	11.43		.450		
o	2.08		.082		2. 4. - CATHODE 3. - ANODE
p	3.81		.150		
R	0.51	0.71	.020	.028	* PART DEPENDENT.
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET

1. - GATE
2. 4. - DRAIN
3. - SOURCE

IGBTs, CoPACK

1. - GATE
2. 4. - COLLECTOR
3. - EMITTER

DIODES

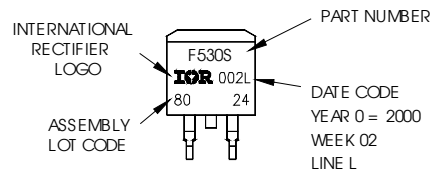
1. - ANODE \*
2. 4. - CATHODE
3. - ANODE

\* PART DEPENDENT.

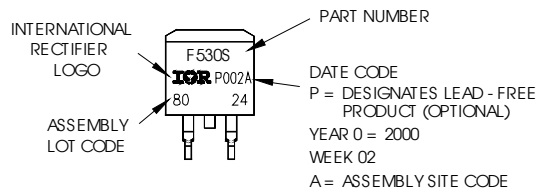
## D<sup>2</sup>Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH  
LOT CODE 8024  
ASSEMBLED ON VW 02, 2000  
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position  
indicates "Lead - Free"

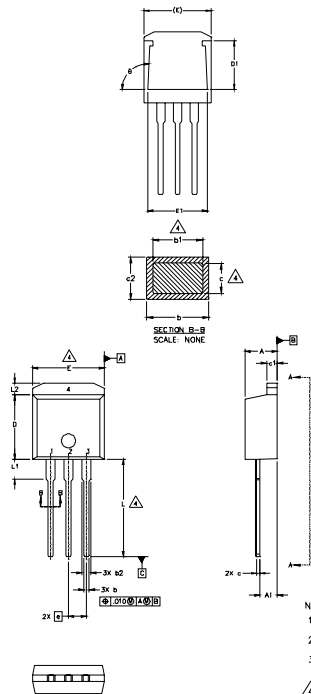


OR





## TO-262 Package Outline



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

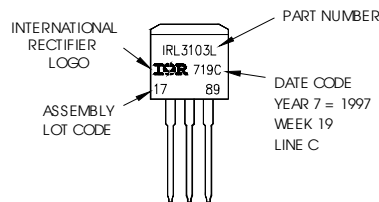
### LEAD ASSIGNMENTS

HEXFET	IGBT
1.- GATE	1- GATE
2.- DRAIN	2- COLLECTOR
3.- SOURCE	3- EMITTER
4.- DRAIN	

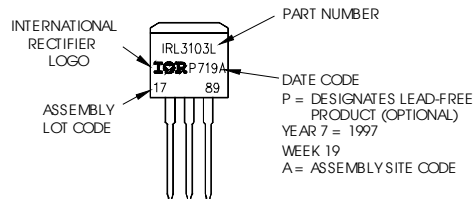
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  2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 (.005") PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  5. CONTROLLING DIMENSION: INCH.

## TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
 Note: "P" in assembly line position indicates "Lead-Free"



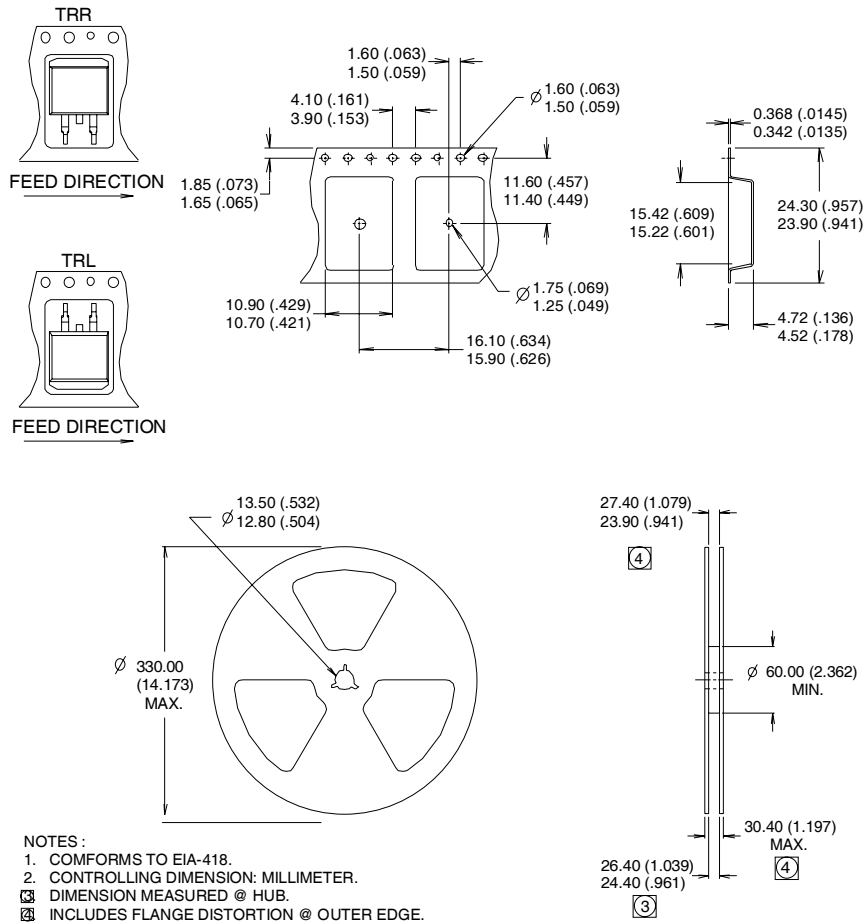
**OR**



# IRF6215S/LPbF

International  
**IR** Rectifier

## D<sup>2</sup>Pak Tape & Reel Information



Data and specifications subject to change without notice.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

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Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>

单击下面可查看定价，库存，交付和生命周期等信息

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